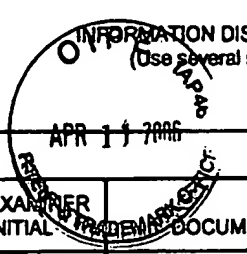
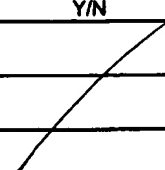


Form PTO-1449		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 97005-US-DIV1		APPLICATION NO. 09/933,960		
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) 				APPLICANT Robert L. Thornton				
				FILING DATE 8/20/2001		GROUP ART UNIT 2828		
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE	CLASS	SUB CLASS			
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Jmf 4/19/06

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